

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) Semiconductor-on-insulator substrate successively comprising a base-(1), a diamond-like carbon layer-(3), a layer made of dielectric material-(4) and a layer made of semi-conducting material-(5) designed to constitute microelectronic elements, the dielectric material-(4) being chosen such that the upper level-(~~E_{di}~~) of the valence band of the dielectric material-(4) is lower than the upper level-(~~E_{ed}~~) of the valence band of the diamond-like carbon-(3) and the semi-conducting material-(5) being chosen such that the upper level-(~~E_{se}~~) of the valence band of the semi-conducting material-(5) is higher than the upper level-(~~E_{ed}~~) of the valence band of the diamond-like carbon-(3), substrate characterized in that it comprises an alumina nucleation layer-(2) disposed between the base (1) and the diamond-like carbon layer-(3).
2. (Currently Amended) Substrate according to claim 1, ~~characterized in that~~ wherein the semi-conducting material-(5) is chosen from silicon, germanium and indium antimonide.
3. (Currently Amended) Substrate according to ~~one of the claims 1 and 2,~~ ~~characterized in that~~ claim 1, wherein the dielectric material-(4) is chosen from alumina (Al_2O_3), hafnium oxide-(~~HfO₂~~) and zirconium oxide-(~~ZrO₂~~).
4. (Currently Amended) Substrate according to claim 3, ~~characterized in that~~ wherein the dielectric material layer is made of monocrystalline alumina.
5. (Currently Amended) Substrate according to ~~any one of the claims 1 to 4,~~ ~~characterized in that~~ claim 1, wherein the nucleation layer-(2) is made of monocrystalline alumina.

6. (Currently Amended) Substrate according to ~~any one of the claims 1 to 5,~~
~~characterized in that claim 1, wherein~~ the dielectric material layer-(4) is formed by
 superposition of two dielectric layers.

7. (Currently Amended) Method for making a substrate according to ~~any one of~~
~~the claims 1 to 6, characterized in that comprises claim 1, comprising~~ preparation of a first
 stack-(11) by:

deposition of the diamond-like carbon layer-(3) on the base-(1), and

deposition of the dielectric material layer-(4) on the diamond-like carbon layer
 (3).

8. (Currently Amended) Method according to claim 7, ~~characterized in that it~~
~~comprises comprising~~ deposition of the nucleation layer-(2) on the base-(1), before deposition
 of the diamond-like carbon layer-(3).

9. (Currently Amended) Method according to ~~one of the claims 7 and 8,~~
~~characterized in that it comprises claim 7, comprising~~ deposition of the semi-conducting
 material-(5) designed to constitute microelectronic elements, after deposition of the dielectric
 material layer-(4).

10. (Currently Amended) Method according to ~~any one of the claims 7 and 8,~~
~~characterized in that it comprises claim 7, comprising~~ preparation of a second stack-(12) by:

deposition of a first additional dielectric layer-(14) on an additional base-(13),

deposition of the semi-conducting-(5) material designed to constitute
 microelectronic elements, on the first additional dielectric layer-(14), and

deposition of a second additional dielectric layer-(15) on the semi-conducting
 material-(5), and

after preparation of the first-(11) and second-(12) stacks, assembly of the first
 (11)-and second-(12) stacks by molecular bonding of the second additional dielectric layer

(15) and of the dielectric material layer-(4), the additional base-(13) then being removed by etching.

11. (Currently Amended) Method according to claim 10, ~~characterized in that it comprises~~ comprising removal of the first additional dielectric layer-(14).

12. (Currently Amended) Method according to ~~one of the claims 7 and 8,~~ claim 7, wherein, a second stack-(12) being formed by an additional substrate comprising a thin film-(18) of the semi-conducting material-(5) designed to constitute microelectronic elements, the thin film-(18) being delineated by a buried zone-(19) fragilized by implantation, the first-(11) and second-(12) stacks are assembled by molecular bonding of the thin film-(18) and of the dielectric material layer-(4), the second stack-(12) being dissociated, after bonding, at the level of the fragilized buried zone-(19).

13. (Currently Amended) Method according to claim 12, ~~characterized in that it comprises~~ comprising thermal oxidation of the thin film-(18), before assembly, so as to form a thermal oxide layer-(20).